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MJE15034 (NPN), MJE15035 (PNP)

Complementary Silicon Plastic Power Transistors

TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high–frequency drivers in audio amplifiers.

Features

- High Current Gain Bandwidth Product
- TO-220 Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 350 | Vdc |
| Collector-Base Voltage | V _{CB} | 350 | Vdc |
| Emitter-Base Voltage | V _{EB} | 5.0 | Vdc |
| Collector Current – Continuous | Ι _C | 4.0 | Adc |
| Collector Current – Peak | I _{CM} | 8.0 | Adc |
| Base Current | I _B | 1.0 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | PD | 50 0.40 | W W/°C |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | PD | 2.0 0.016 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |
| ESD – Human Body Model | HBM | 3B | V |
| ESD – Machine Model | MM | С | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.5 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 62.5 | °C/W |

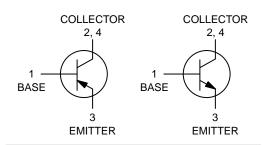


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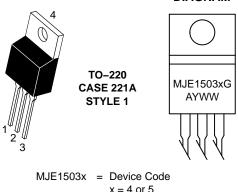
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4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS

COMPLEMENTARY







| x = 4 01 J |
|-------------------|
| = Location Code |
| = Year |
| = Work Week |
| = Pb–Free Package |
| |

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|---------------------|-----------------|
| MJE15034G | TO–220 (Pb–Free) | 50 Units / Rail |
| MJE15035G | TO–220 (Pb–Free) | 50 Units / Rail |

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJE15034 (NPN), MJE15035 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

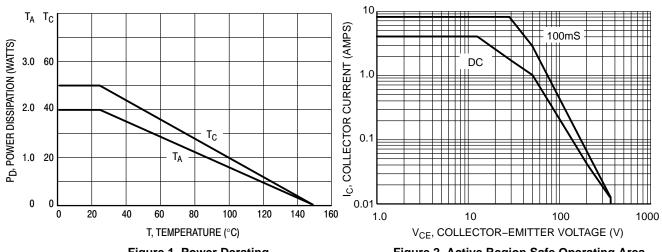
| Characteristic | Symbol | Min | Max | Unit | | | |
|---|---|-----------------------|------------------------|------|------|--|--|
| OFF CHARACTERISTICS | | | | | | | |
| Collector-Emitter Sustaining Voltage (Note 1) | $(I_{C} = 10 \text{ mAdc}, I_{B} = 0)$ | V _{CEO(sus)} | 350 | - | Vdc | | |
| Collector Cutoff Current | $(V_{CB} = 350 \text{ Vdc}, I_E = 0)$ | I _{CBO} | - | 10 | μAdc | | |
| Emitter Cutoff Current | $(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$ | I _{EBO} | - | 10 | μAdc | | |
| ON CHARACTERISTICS (Note 1) | | | | | | | |
| DC Current Gain | | h _{FE} | 100 100 50 10 | | - | | |
| Collector-Emitter Saturation Voltage | $(I_{C} = 1.0 \text{ Adc}, I_{B} = 0.1 \text{ Adc})$ | V _{CE(sat)} | - | 0.5 | Vdc | | |
| Base-Emitter On Voltage | $(I_{C} = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$ | V _{BE(on)} | - | 1.0 | Vdc | | |
| DYNAMIC CHARACTERISTICS | | | - | | • | | |
| | | | | | | | |

| Current Gain – Bandwidth Product (Note 2) | f _T | | | MHz |
|---|----------------|----|---|-----|
| $(I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1.0 \text{ MHz})$ | | 30 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.







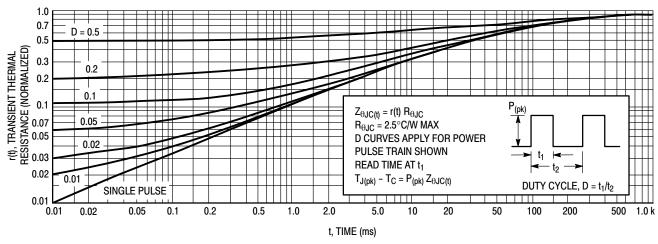
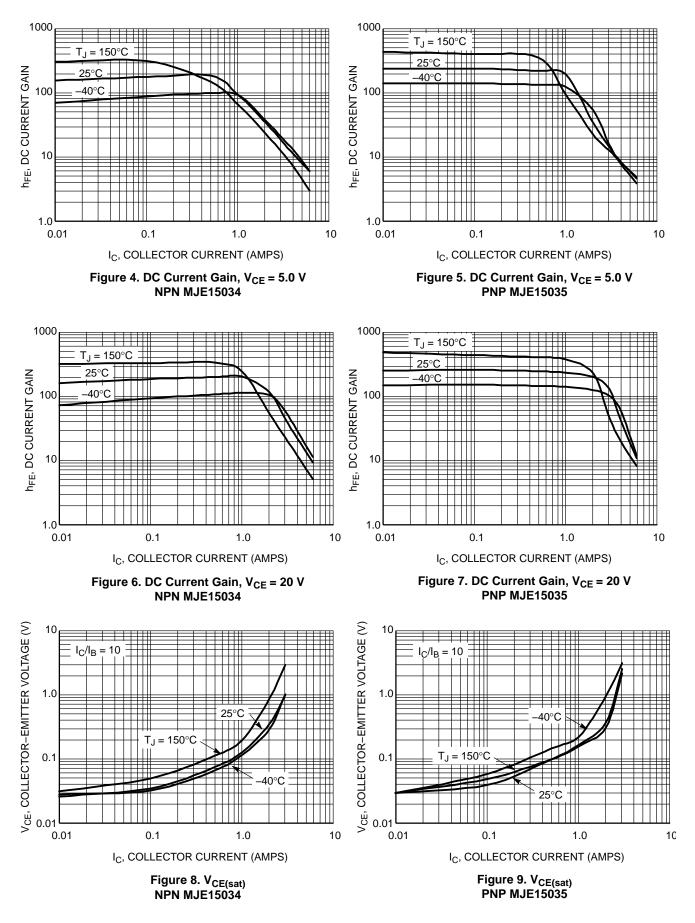
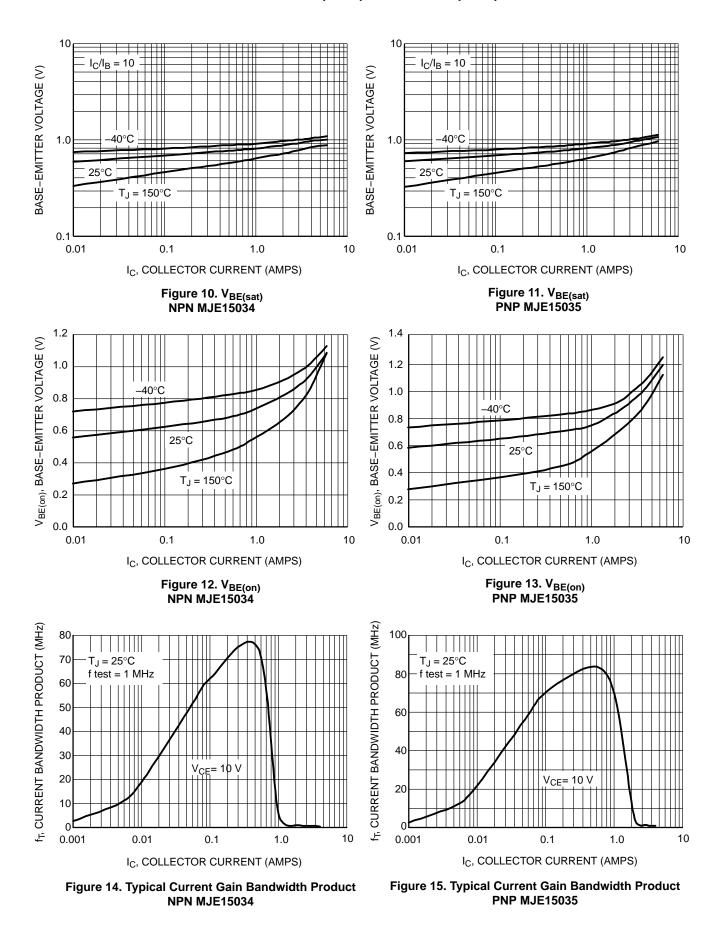


Figure 3. Thermal Response

MJE15034 (NPN), MJE15035 (PNP)



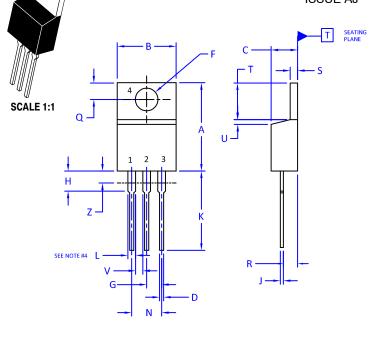
MJE15034 (NPN), MJE15035 (PNP)



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TO-220 CASE 221A-09 ISSUE AJ



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.

2. CONTROLLING DIMENSION: INCHES

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| | INCHES | | MILLIME | ETERS | |
|-----|-----------|-------|---------|-------|--|
| DIM | MIN. MAX. | | MIN. | MAX. | |
| А | 0.570 | 0.620 | 14.48 | 15.75 | |
| В | 0.380 | 0.415 | 9.66 | 10.53 | |
| С | 0.160 | 0.190 | 4.07 | 4.83 | |
| D | 0.025 | 0.038 | 0.64 | 0.96 | |
| F | 0.142 | 0.161 | 3.60 | 4.09 | |
| G | 0.095 | 0.105 | 2.42 | 2.66 | |
| Н | 0.110 | 0.161 | 2.80 | 4.10 | |
| J | 0.014 | 0.024 | 0.36 | 0.61 | |
| К | 0.500 | 0.562 | 12.70 | 14.27 | |
| L | 0.045 | 0.060 | 1.15 | 1.52 | |
| Ν | 0.190 | 0.210 | 4.83 | 5.33 | |
| Q | 0.100 | 0.120 | 2.54 | 3.04 | |
| R | 0.080 | 0.110 | 2.04 | 2.79 | |
| S | 0.045 | 0.055 | 1.15 | 1.41 | |
| Т | 0.235 | 0.255 | 5.97 | 6.47 | |
| U | 0.000 | 0.050 | 0.00 | 1.27 | |
| V | 0.045 | | 1.15 | | |
| Z | | 0.080 | | 2.04 | |

| STYLE 1: PIN 1. 2. 3. 4. | COLLECTOR EMITTER | STYLE 2: PIN 1. 2. 3. 4. | COLLECTOR | | • | STYLE 4: PIN 1. 2. 3. 4. | MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2 |
|--------------------------------------|----------------------|---------------------------------------|--------------------------------------|----------|--------------------------------------|--------------------------------------|---|
| STYLE 5: PIN 1. 2. 3. 4. | DRAIN SOURCE | 2. 3. | ANODE CATHODE ANODE CATHODE | 2. 3. | CATHODE ANODE CATHODE ANODE | 2. 3. | CATHODE ANODE EXTERNAL TRIP/DELAY ANODE |
| STYLE 9: PIN 1. 2. 3. 4. | COLLECTOR EMITTER | STYLE 10: PIN 1. 2. 3. 4. | GATE SOURCE DRAIN | | DRAIN SOURCE GATE | STYLE 12 PIN 1. 2. 3. 4. | MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED |

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